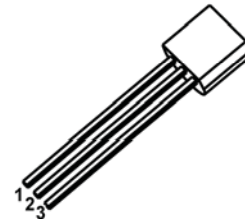
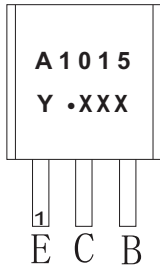


BIPOLAR TRANSISTOR (PNP)
FEATURES

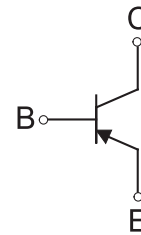
- Power dissipation


TO - 92

1. EMITTER 2. COLLECTOR 3. BASE

MARKING


A1015=Device code
 Solid dot=Green molding compound device,
 if none,the normal device
 Y=Rank of h_{FE} ,
 XXX=Code

Equivalent Circuit

ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA1015	TO-92	Bulk	10000
2SA1015-TA	TO-92	Tape	2000

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_D	Collector Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	312	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS $T_a=25^{\circ}\text{C}$ unless otherwise specified

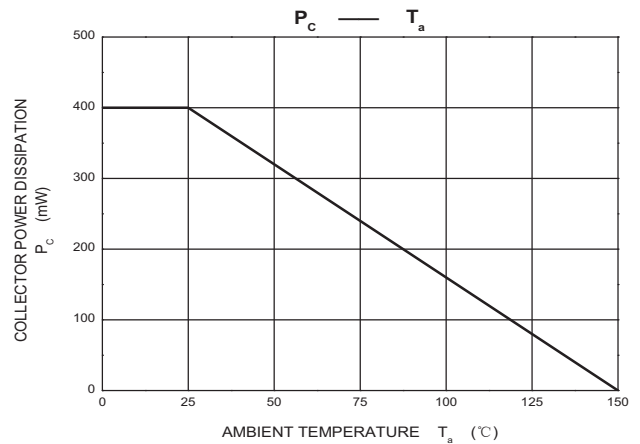
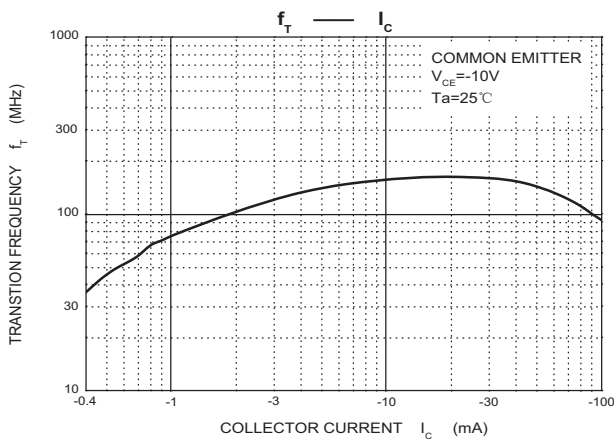
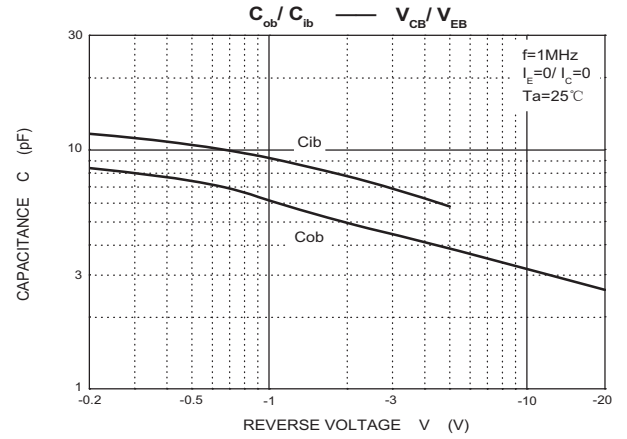
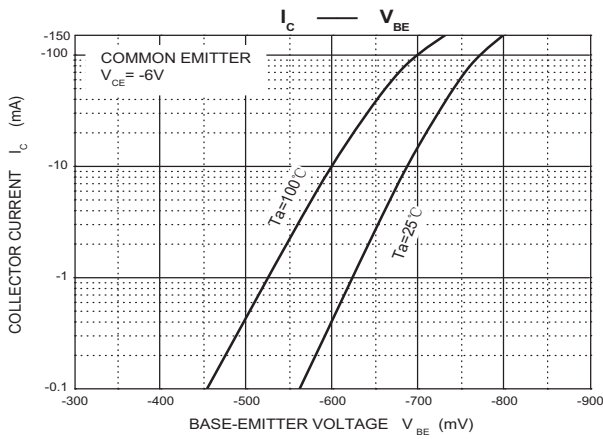
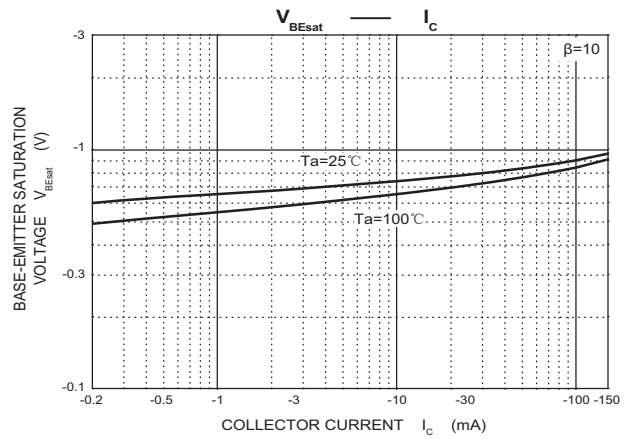
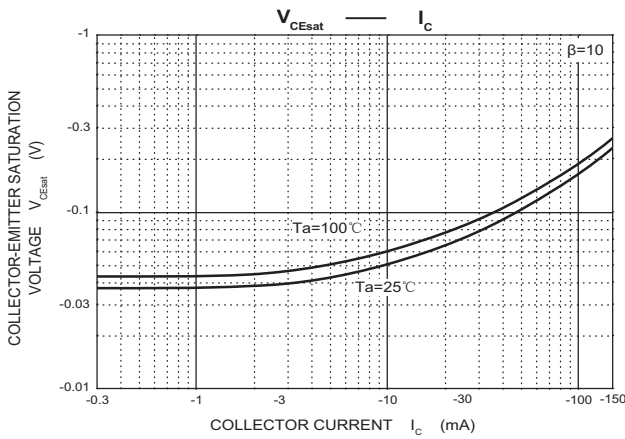
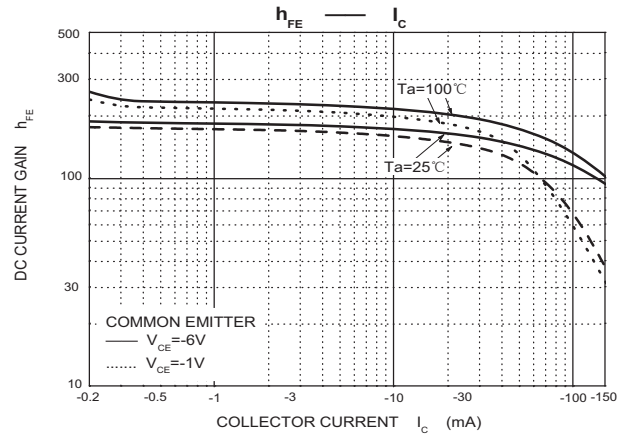
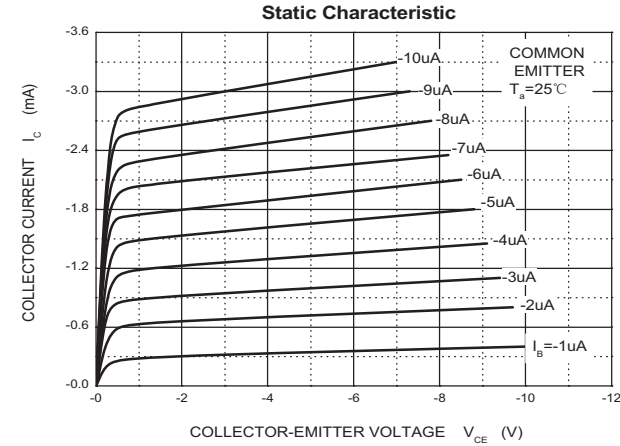
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1\text{mA}, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -50\text{V}, I_B = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6\text{V}, I_C = -2\text{mA}$	70		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-1.1	V
Transition frequency	f_T	$V_{CE} = -10\text{V}, I_C = -1\text{mA}$ $f = 30\text{MHz}$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			7	pF
Noise figure	NF	$V_{CE} = -6\text{V}, I_C = -0.1\text{mA}$, $f = 1\text{kHz}, R_G = 10\text{k}\Omega$			6	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR	BL
Range	70-140	120-240	200-400	350-700

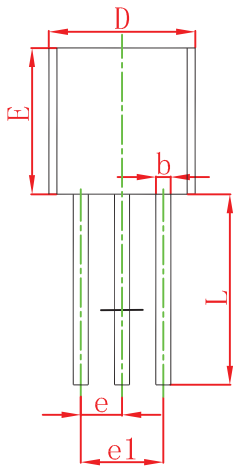
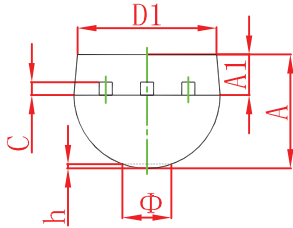
BIPOLAR TRANSISTOR (PNP)

Typical Characteristics



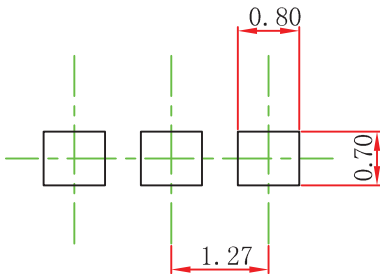
BIPOLAR TRANSISTOR (PNP)

TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout



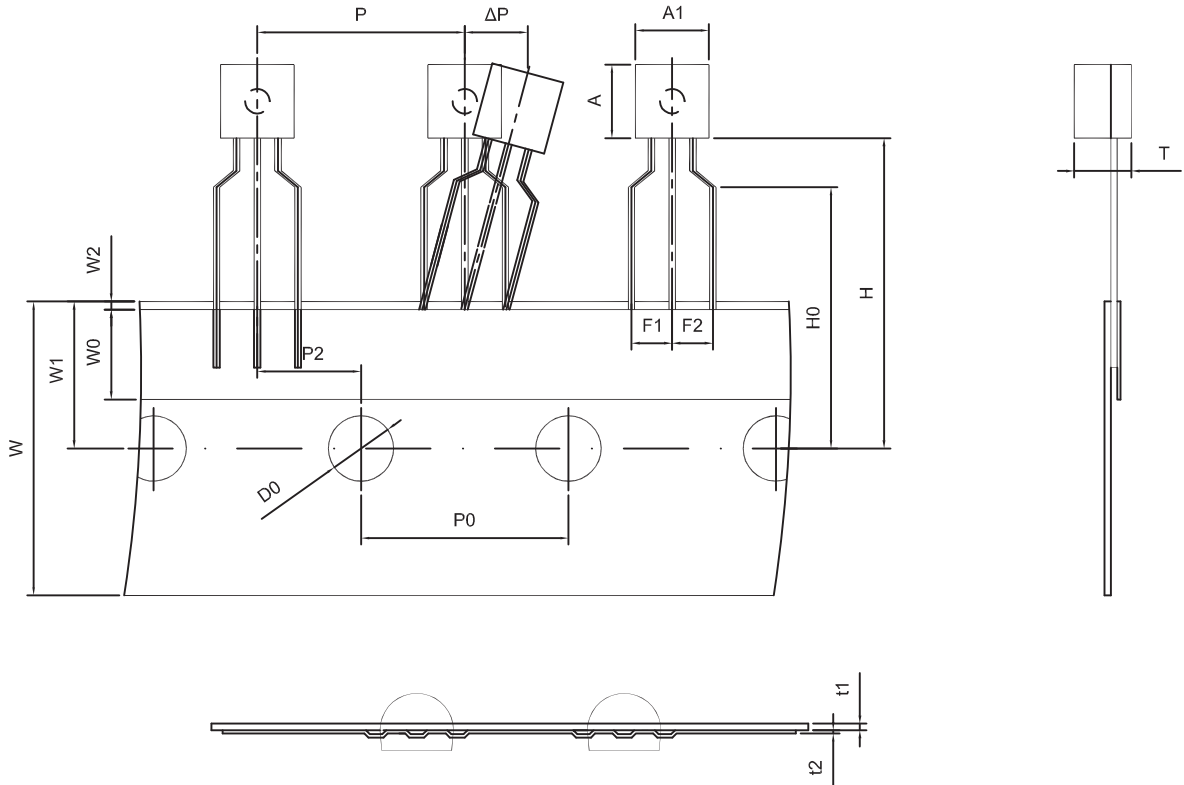
Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05mm.
3. The pad layout is for reference purposes only.

BIPOLAR TRANSISTOR (PNP)

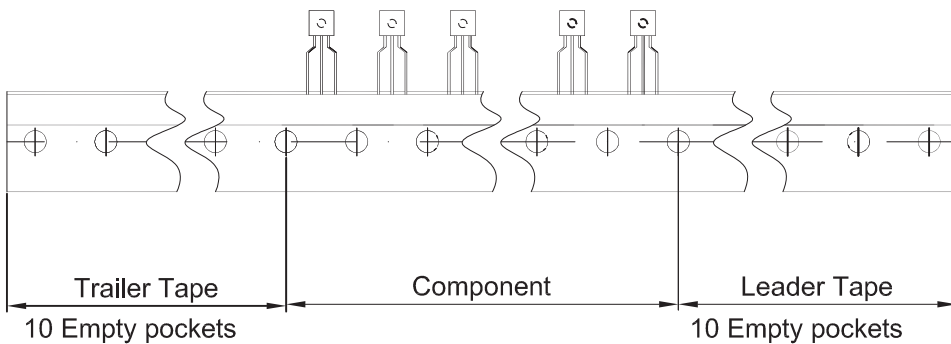
TO-92 Tape and Reel

TO-92 PACKAGE TAPEING DIMENSION



Dimensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250